

# GMN08006M

**GOOD-ARK Electronics** 

## N-Channel 60V (D-S) Power MOSFET

#### **Features**

- 100% Avalanche Tested
- Extremely Low Losses with Low FOM Rdson\*Qg
- Halogen Free, Pb-Free
- RoHS Compliant



**PDFN5060** 

4 G O-

D 5, 6, 7, 8

S 1, 2, 3

#### **Applications**

- DC-DC
- Motors, lamps
- Power switching

Absolute Maximum Ratings (TJ=25°C unless otherwise noted)						
Parameter		Symbol	Value	Unit		
Drain Source Voltage		V <sub>DS</sub>	60	V		
Gate Source Voltage		V <sub>GS</sub>	±20	V		
Drain Current, Continuous V <sub>GS</sub> =10V <i>(Note 1)</i>	T <sub>c</sub> =25°C	ID	80	А		
Drain Current, Pulsed (Note 2)	I <sub>DM</sub>	320	А			
Single Avalanche Energy @ L=0.3mH		E <sub>AS</sub>	184	mJ		
Power Dissipation(Note 3)	T <sub>C</sub> =25°C	PD	108	W		
Operating Junction/ Storage Temperature Range		TJ/ T <sub>STG</sub>	-55 to +150	°C		

Note 1: Calculated continuous current based on maximum allowable junction temperature. Note 2: Repetitive rating; pulse width limited by max. junction temperature.

Thermal Characteristics						
Parameter	Symbol	Мах	Unit			
Thermal Resistance Junction to Case (Note 3)	R <sub>thJC</sub>	1.4	°C/W			
Thermal Resistance Junction to Ambient (Note 4)	R <sub>thJA</sub>	92	°C/W			

Note 3: The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance. Note 4: The value of R<sub>BJA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25 °C.



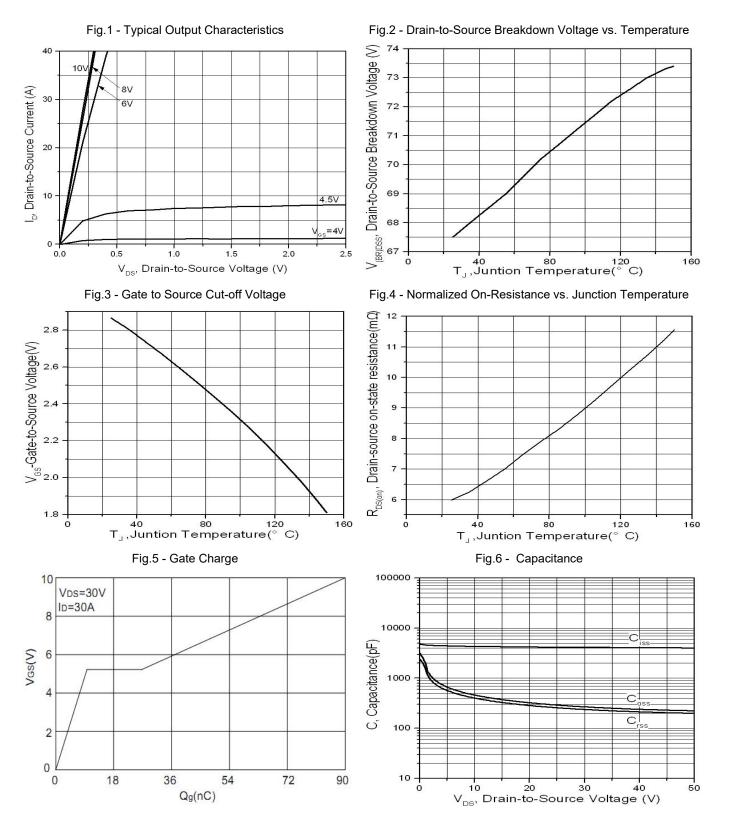
Electrical Characteristics (T <sub>J</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250µA	60			V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1.0	uA
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250uA	2		4	V
Gate Leakage Current	I <sub>GSS</sub>	$V_{GS}=\pm 20V, V_{DS}=0V$			±100	nA
Drain-Source On-state Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A		5.4	8	mΩ
Total Gate Charge	Qg			89		
Gate-Source Charge	Q <sub>gs</sub>	I <sub>D</sub> = 30A, V <sub>DS</sub> =30V, V <sub>GS</sub> = 10V		8		nC
Gate-Drain Charge	Q <sub>gd</sub>			16		
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =33V, I <sub>D</sub> =30A, R <sub>GEN</sub> =2.2Ω		18.3		
Turn-on Rise Time	tr			33.5		
Turn-off Delay Time	t <sub>d(off)</sub>			37.5		ns
Turn-off Fall Time	t <sub>f</sub>			9.7		
Input Capacitance	C <sub>iss</sub>	V <sub>GS=</sub> 0V, V <sub>DS</sub> =50V, f=1MHz		4040		
Output Capacitance	Coss			223		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			119		

<b>Reverse Diode Characteristics</b> (T <sub>J</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Continuous Source Current (Body Diode)	ls	T <sub>C</sub> =25°C			80	A
Pulsed Source Current (Body Diode)	I <sub>SM</sub>				320	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =30A, V <sub>GS</sub> =0V			1.2	V
Reverse Recovery Time	Trr	- I <sub>F</sub> =30A, di/dt = 100 A/µs		32		ns
Reverse Recovery Charge	Qrr			45		nC



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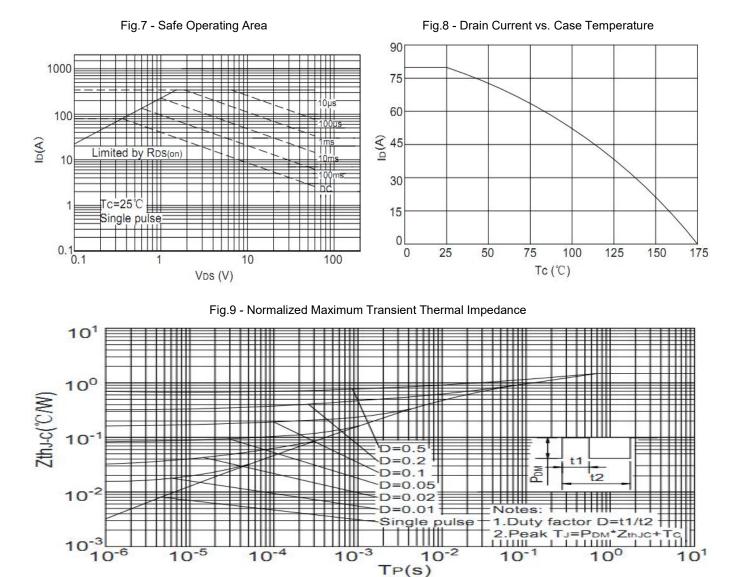
#### **Typical Characteristics Curves** (T<sub>J</sub> = 25°C unless otherwise noted)





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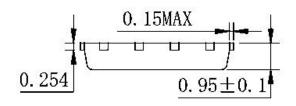
#### **Typical Characteristics Curves** (T<sub>J</sub> = 25°C unless otherwise noted)

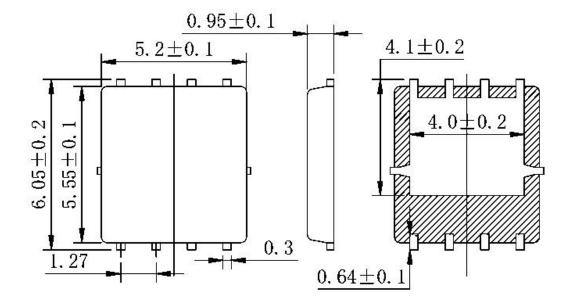




### Package Outline Dimensions (Unit: millimeters)

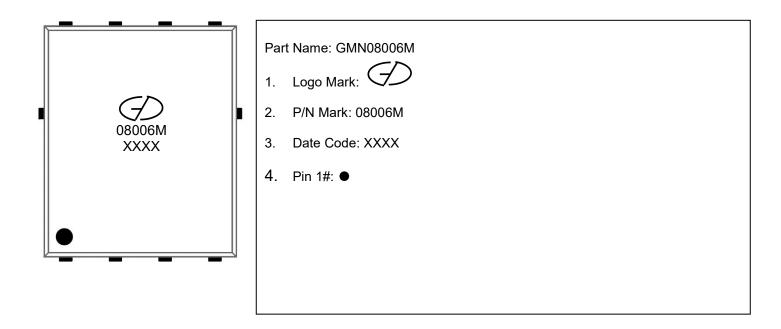
**PDFN5060** 







### Marking Outline





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